

Three quadrant triacs high commutation

BTA204W series B and C

GENERAL DESCRIPTION

Passivated high commutation triacs in a plastic envelope suitable for surface mounting intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commute the full rated rms current at the maximum rated junction temperature without the aid of a snubber.

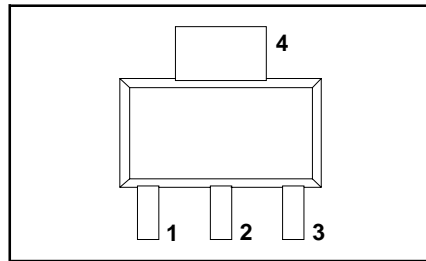
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | MAX. | UNIT |
|--------------|--------------------------------------|--------------|--------------|--------------|------|
| | | 500B 500C | 600B 600C | 800B 800C | |
| V_{DRM} | Repetitive peak off-state voltages | 500 | 600 | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | 1 | 1 | 1 | A |
| I_{TSM} | Non-repetitive peak on-state current | 10 | 10 | 10 | A |

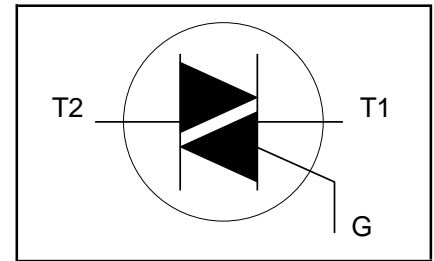
PINNING - SOT223

| PIN | DESCRIPTION |
|-----|-----------------|
| 1 | main terminal 1 |
| 2 | main terminal 2 |
| 3 | gate |
| tab | main terminal 2 |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | | UNIT |
|--------------|--------------------------------------|---|------|--------------------------|--------------------------|-------------|------------------|
| | | | | -500 500 ¹ | -600 600 ¹ | -800 800 | |
| V_{DRM} | Repetitive peak off-state voltages | | - | | | | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{sp} \leq 108^\circ\text{C}$ | - | 1 | | | A |
| I_{TSM} | Non-repetitive peak on-state current | full sine wave; $T_j = 25^\circ\text{C}$ prior to surge | - | 10 | | | A |
| | | $t = 20\text{ ms}$ | - | 11 | | | A |
| | | $t = 16.7\text{ ms}$ | - | 0.5 | | | A ² s |
| | | $t = 10\text{ ms}$ | - | 100 | | | A/ μs |
| I_{GM} | Peak gate current | $I_{TM} = 1.5\text{ A};$ $I_G = 0.2\text{ A};$ $dI_G/dt = 0.2\text{ A}/\mu\text{s}$ | - | 2 | | | A |
| V_{GM} | Peak gate voltage | | - | 5 | | | V |
| P_{GM} | Peak gate power | | - | 5 | | | W |
| $P_{G(AV)}$ | Average gate power | over any 20 ms period | - | 0.5 | | | W |
| T_{stg} | Storage temperature | | -40 | 150 | | | $^\circ\text{C}$ |
| T_j | Operating junction temperature | | - | 125 | | | $^\circ\text{C}$ |

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ μs .

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------|--|---|------|-----------|------|------------|
| $R_{th\ j-sp}$ | Thermal resistance junction to solder point | full or half cycle | - | - | 15 | K/W |
| $R_{th\ j-a}$ | Thermal resistance junction to ambient | pcb mounted; minimum footprint pcb mounted; pad area as in fig:2 | - | 156 70 | - | K/W K/W |

STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|----------|-----------------------------------|---|------|------------|----------------|----------------|----------------|
| | | BTA204W- | | | ...B | ...C | |
| I_{GT} | Gate trigger current ² | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G- | - | - | 50 50 50 | 35 35 35 | mA mA mA |
| I_L | Latching current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G- | - | - | 30 45 30 | 20 30 20 | mA mA mA |
| I_H | Holding current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ | - | - | 30 | 20 | mA |
| V_T | On-state voltage | $I_T = 2\text{ A}$ | - | 1.2 | 1.5 | | V |
| V_{GT} | Gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ $V_D = 400\text{ V}; I_T = 0.1\text{ A};$ $T_j = 125\text{ °C}$ | - | 0.7 0.4 | 1.5 - | | V V |
| I_D | Off-state leakage current | $V_D = V_{DRM(max)}; T_j = 125\text{ °C}$ | - | 0.1 | 0.5 | | mA |

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | UNIT | |
|---------------|---|--|------|------|-------------|-------------|
| | | BTA204W- | | | ...B | ...C |
| dV_D/dt | Critical rate of rise of off-state voltage | $V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform; gate open circuit | 1000 | 1000 | - | V/ μ s |
| dI_{com}/dt | Critical rate of change of commutating current | $V_{DM} = 400\text{ V}; T_j = 125\text{ °C}; I_{T(RMS)} = 1\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ gate open circuit | 6 | 3 | - | A/ms |
| t_{gt} | Gate controlled turn-on time | $I_{TM} = 12\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$ | - | - | 2 | μ s |

² Device does not trigger in the T2-, G+ quadrant.

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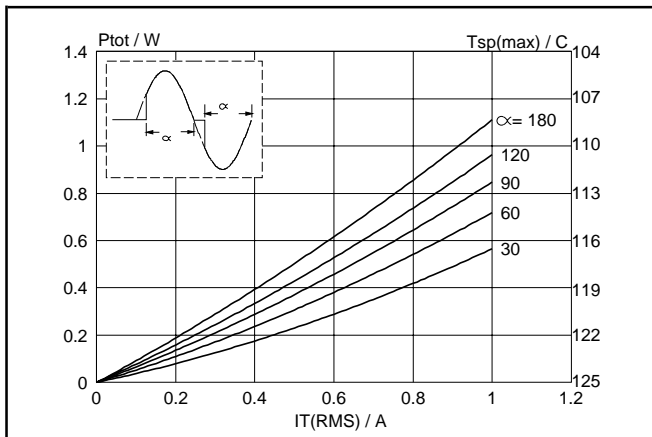


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

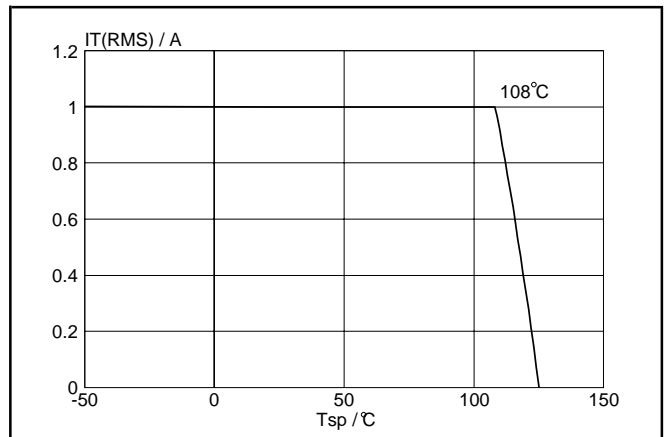


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus solder point temperature T_{sp} .

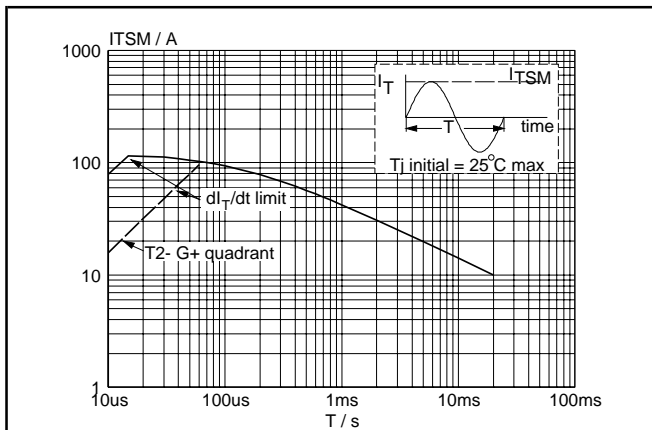


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20ms$.

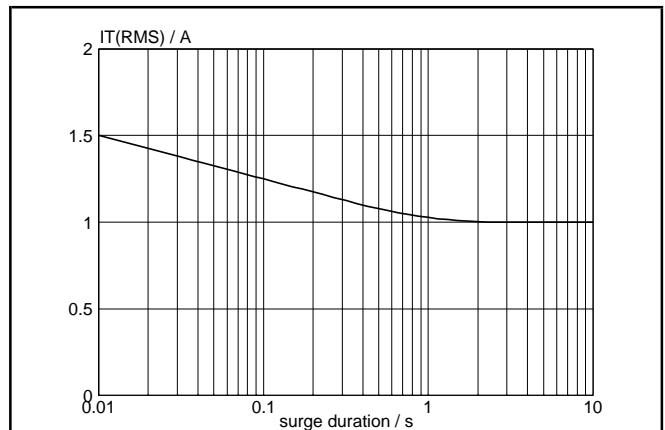


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50 Hz$; $T_{sp} \leq 108^\circ C$.

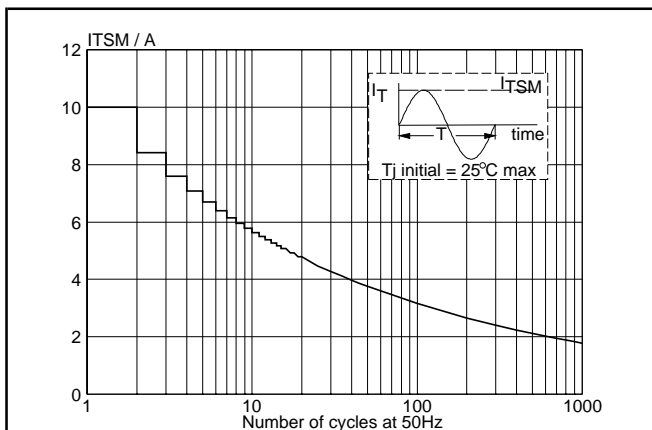


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50 Hz$.

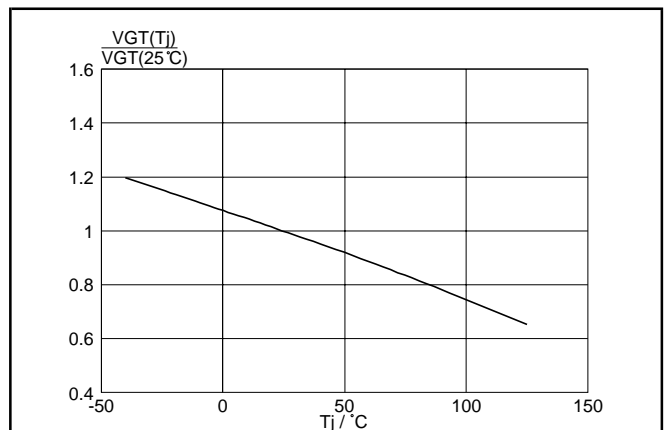
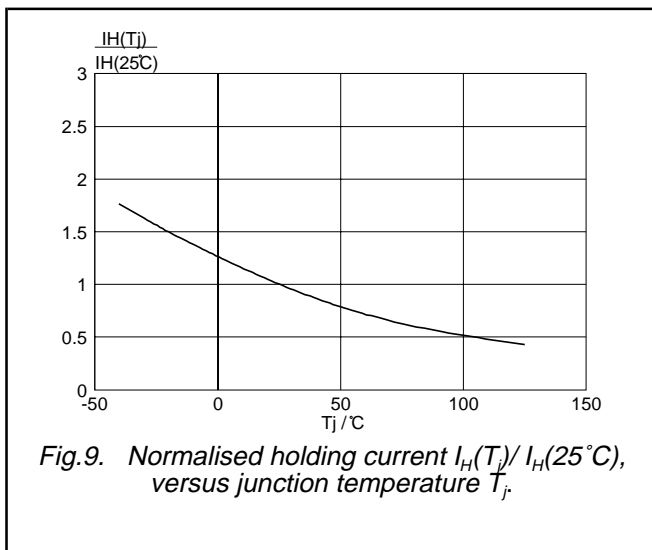
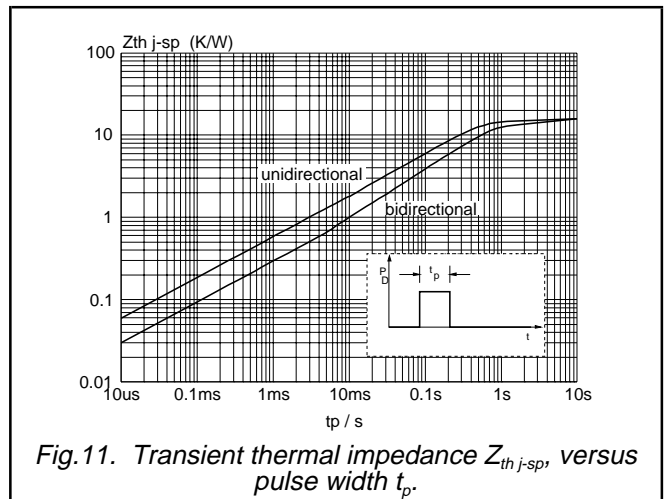
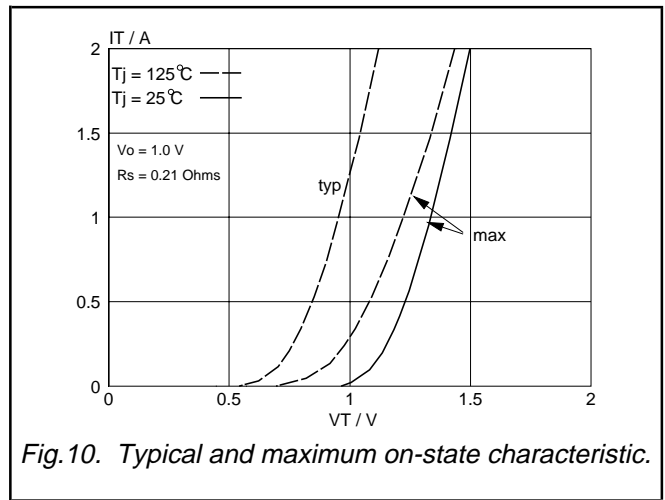
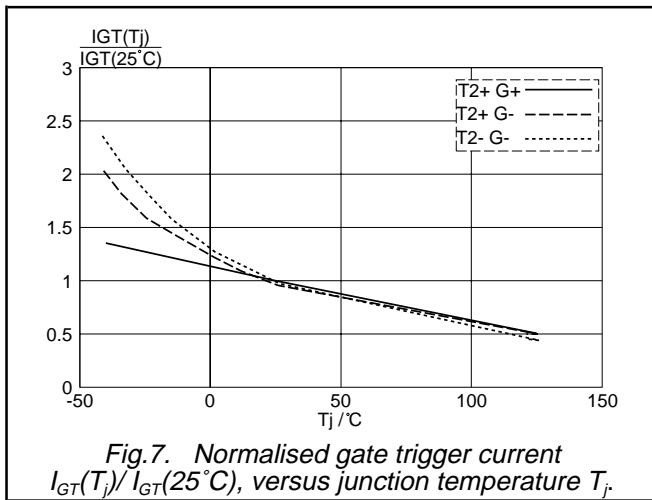


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ C)$, versus junction temperature T_j .

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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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